

Product / Process Change Notice

Parts Affected:

Chip process CP188 (NPN) and chip process CP588 (PNP) silicon, small signal transistors, wafers, and bare die.

Extent of Change:

The CP188 and CP588 wafer processes have been discontinued and replaced with the CP388X and CP788X process respectively.

The overall wafer diameter was increased from 4 inch to 5 inch.

The overall wafer thickness was reduced from 9 mils to 5.9 mils.

The topside bond pad metallization (Al) was reduced from 30,000 Å to 17,000Å.

The backside metallization (Au) was reduced from 18,000Å to 9,000Å.

The die size and die pattern were changed; see figures 1 and 2 for details.

Reason for Change:

Process transfer from the 4" wafer fab to the 5" wafer fab.

Effect of Change:

The new wafer processes meet or exceed the electrical performance of the prior processes.

Qualification:

Standard evaluation and qualifications completed resulting in no performance differences compared to current product.

Effective Date of Change:

Existing inventory will be shipped until depleted.

Part Numbers Affected and Sample Availability:

Please contact Salesperson or Manufacturer's Representative.

Figures:

Figure 1: CP188 and CP588 Chip Geometry (Discontinued)

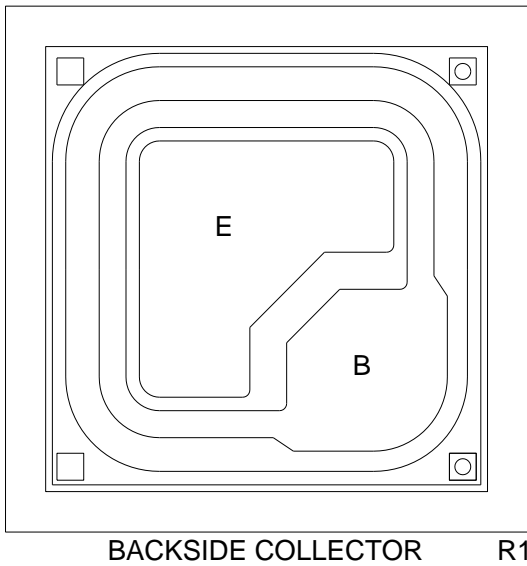
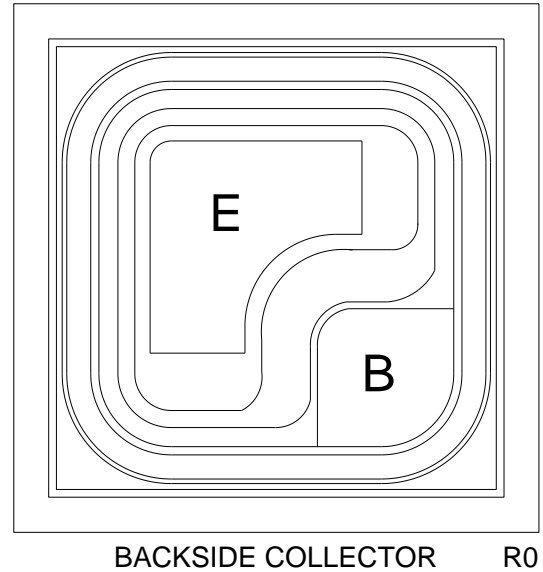


Figure 2: CP388X and CP788X Chip Geometry



Wafer Diameter:	4 inch
Die Size:	14.6 x 14.6 mils
Die Thickness:	9.0 mils
Bond Pad Size (Emitter):	5.5 x 5.5 mils
Bond Pad Size (Base):	3.9 x 3.9 mils
Topside Metal:	Al (30,000Å)
Backside Metal:	Au (18,000Å)

Wafer Diameter:	5 inch
Die Size:	13.7 x 13.7 mils
Die Thickness:	5.9 mils
Bond Pad Size (Emitter):	5.5 x 5.5 mils
Bond Pad Size (Base):	3.9 x 3.9 mils
Topside Metal:	Al (17,000Å)
Backside Metal:	Au (9,000Å)